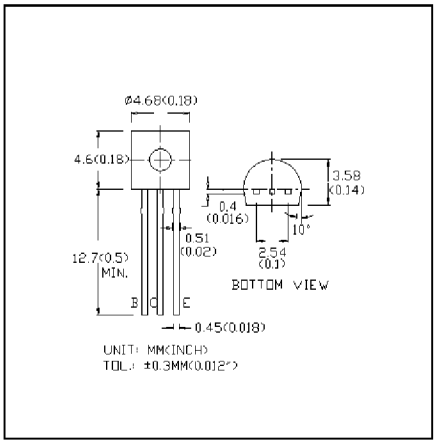
MICRO ELECTRONICS

2N5367

PNP
SILICON
TRANSISTOR

DESCRIPTION

2N5367 is PNP silicon planar transistor use in general purpose consumer and industrial amplifier and switching applications.



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V_{CEO}	40V
Collector-Emitter Voltage	V_{CBO}	40V
Emitter-Base Voltage	V_{EBO}	4V
Collector Current	I_C	300mA
Continuous Power Dissipation	P_d	360mW
Operating & Storage Junction Temperature	T_j, T_{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	LV_{CEO*}	40		V	I_C=10mA	I_B=0
Collector Cutoff Current	I_{CBO}		100	nA	V_{CB}=40V	I_E=0
Collector Cutoff Current	I_{CES}		100	nA	V_{CB}=40V	V_{EB}=0
Emtter Cutoff Current	I_{EBO}		10	μA	V_{EB}=4V	I_C=0
D.C. Current Gain	H_{FE*}	200			I_C=2mA	V_{CE}=10V
		250	500		I_C=50mA	V_{CE}=1V
		75			I_C=300mA	V_{CE}=5V
Base-Emitter Voltage	V_{BE}		0.8	V	I_C=2mA	V_{CE}=10V
Collector-Emitter Saturation Voltage	$V_{CE(sat)*}$		0.25	V	I_C=50mA	I_B=2.5mA
			1	V	I_C=300mA	I_B=30mA
Base-Emitter Saturation Voltage	$V_{BE(sat)*}$		1.1	V	I_C=50mA	I_B=2.5mA
			2	V	I_C=300mA	I_B=30mA
Small Signal Current Gain	h_{fe}	200			I_C=2mA	V_{CE}=10V
					f=1kHz	
Output Capacitance	C_{ob}		8	pF	V_{CB}=10V	f=1MHz
Input Capacitance	C_{ib}		35	pF	V_{EB}=0.5V	f=1MHz
Current Gain-Bandwidth Product	f_T	200	TYP	pF	I_C=2mA	V_{CE}=10V

* Pulse test : pulse width <300μS, duty cycle < 2%.

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